<u>S/N 10/765,301</u> <u>PATENT</u>

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Terrence C. Leslie Examiner: Matthew C. Landau

Serial No.: 10/765,301 Group Art Unit: 2815

Filed: January 27, 2004 Docket: 303.860US1

Title: SELECTIVE EPITAXY VERTICAL INTEGRATED CIRCUIT COMPONENTS

AND METHODS

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants hereby authorize the Commissoner to charge the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p), to Deposit Account No. 19-0743. Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

TERRENCE C. LESLIE

By his Representatives,

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Date 4/Vlay 06

Timothy B Clise Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being filed using the USBTO's electronic filing system EFS-Web, and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this day of May, 2006.

JUDY DETN

Name

Signature 1)

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Substitute for form 1449A/PTO	Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/765,301	
(Use as many sheets as necessary)	Filing Date	January 27, 2004	
	First Named Inventor	Leslie, Terrence	
	Group Art Unit	2815	
	Examiner Name	Landau, Matthew	
Sheet 1 of 1	Attorney Docket No: 3	803.860US1	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate		
	US-6,687,146	02/03/2004	Kurjanowicz, Wlodek, et al.	01/31/2002		

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T²

		R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	] T²
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Item (book, magazine, journal, serial, symposlum, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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**EXAMINER** 

**DATE CONSIDERED**